

Supporting information

The chalcogenide perovskite BaZrS₃: Thin film growth by sputtering and rapid thermal processing

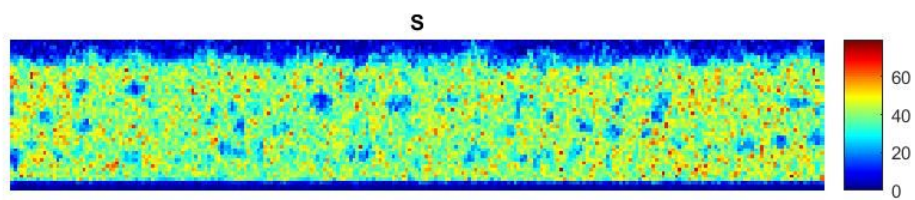
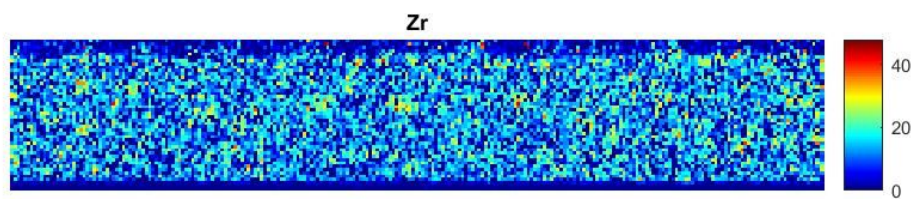
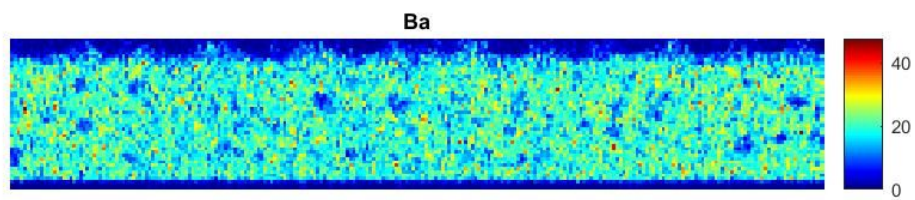
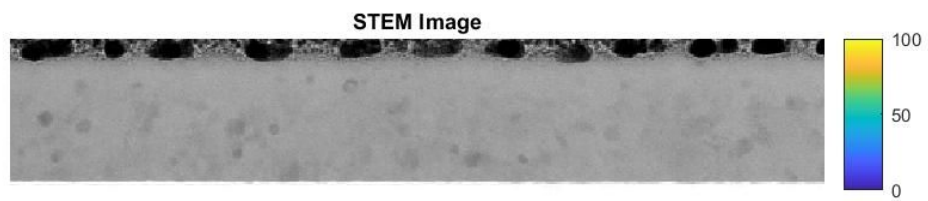
Corrado Comparotto^{}, Alexandra Davydova, Tove Ericson, Lars Riekehr, Marcos V. Moro,*

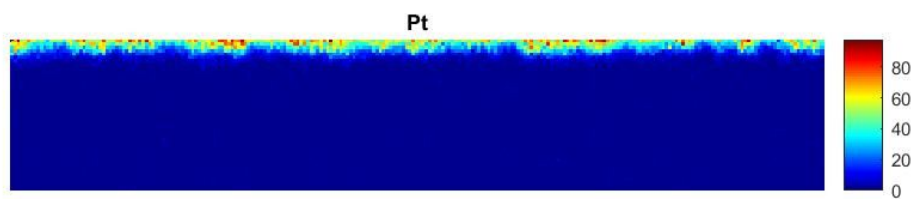
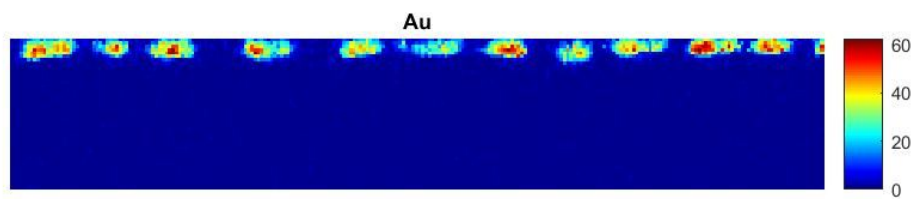
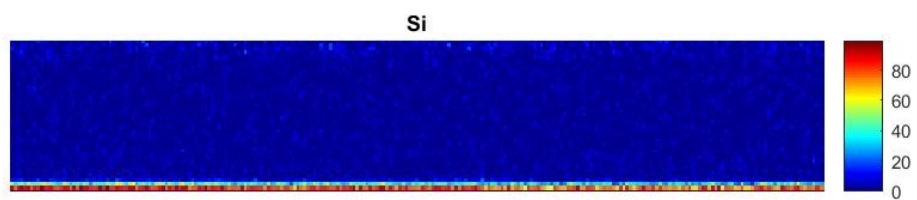
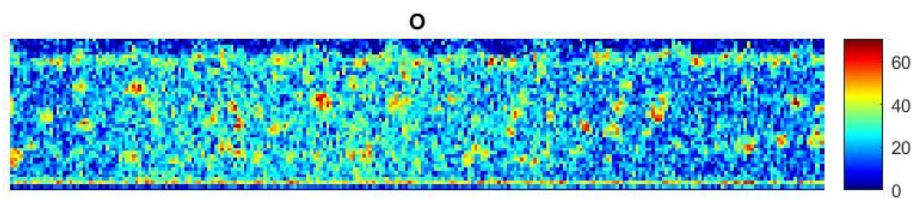
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Herein additional STEM bright field images and EDS maps of Ba, Zr, S, O, Si, Au, Pt, Pd, and F are reported. They were measured at 100°, 120°, and 180° on a compositionally graded sample annealed at 900°C. The EDS maps were recorded on the same area where STEM was performed.





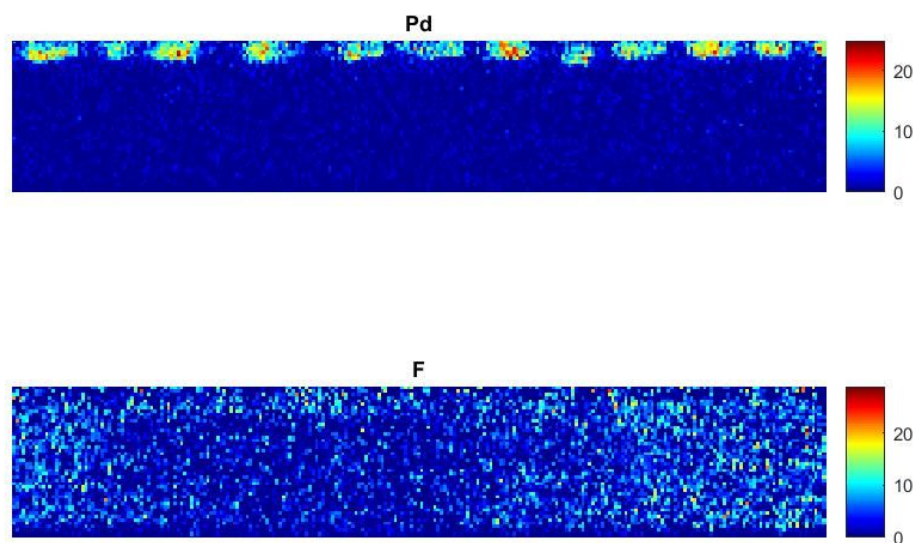
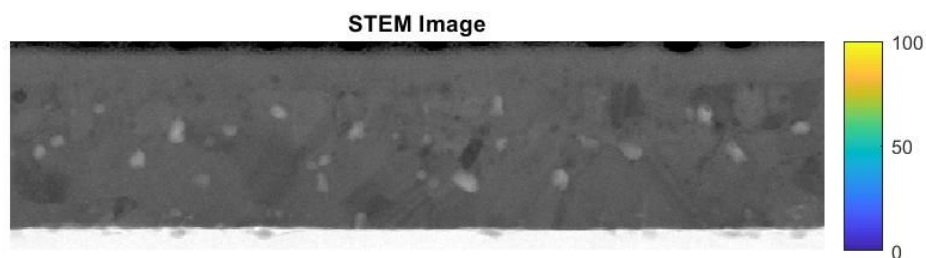
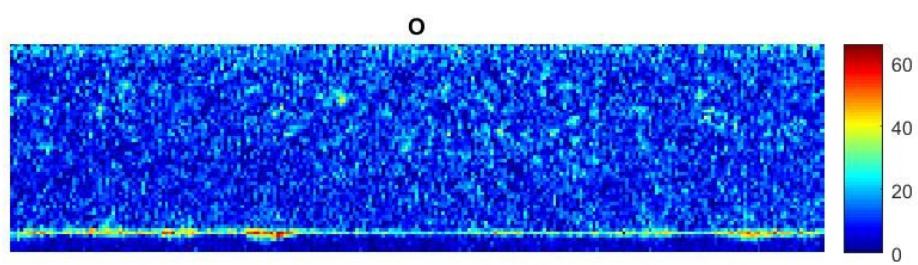
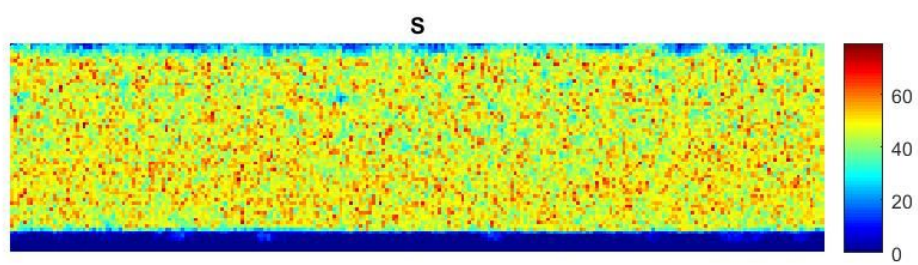
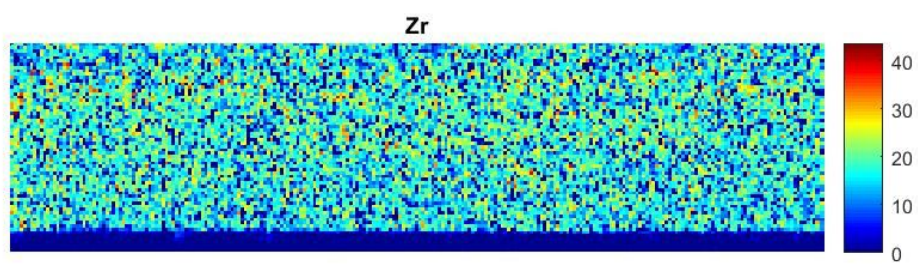
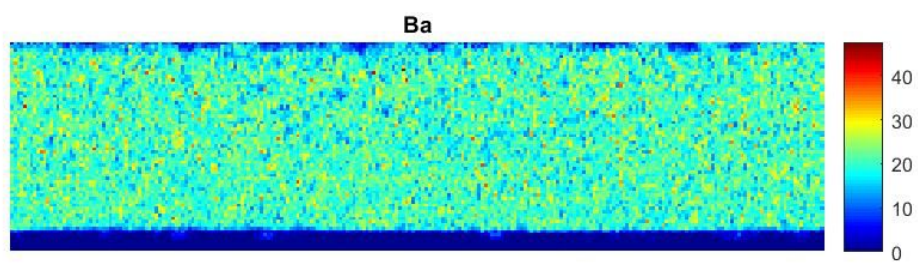
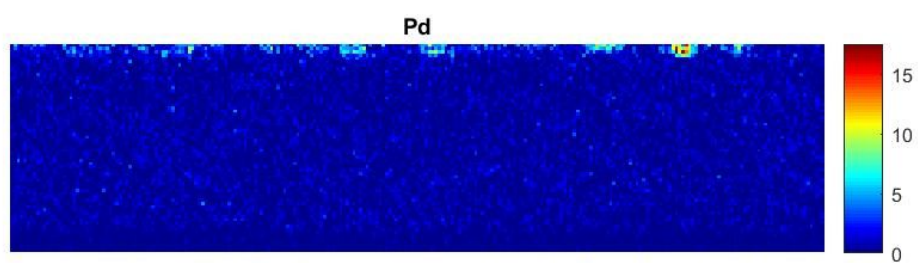
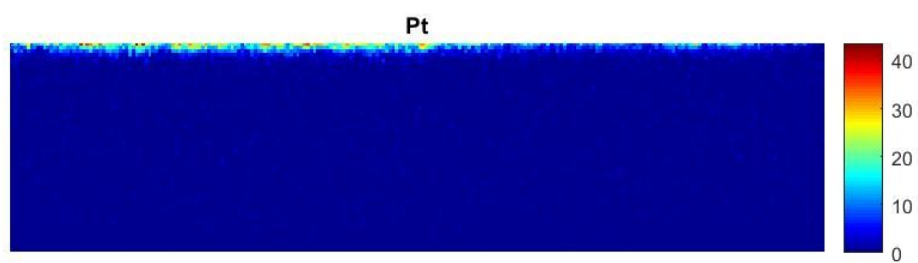
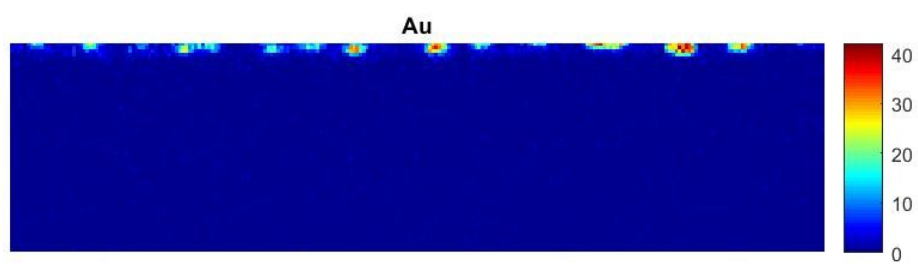
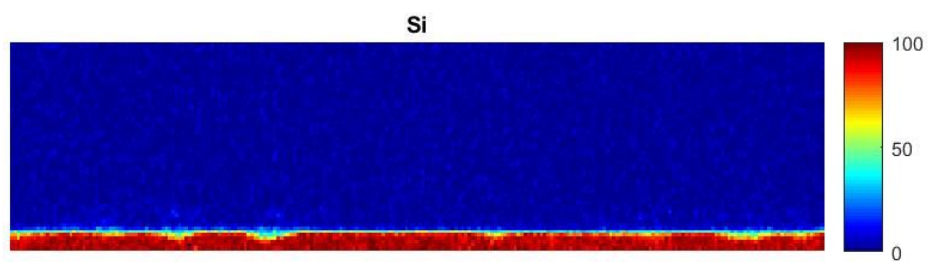


Figure S1. STEM bright field image measured at 100° on a compositionally graded sample annealed at 900°C ; EDS maps of different elements recorded on the same area where STEM was performed.







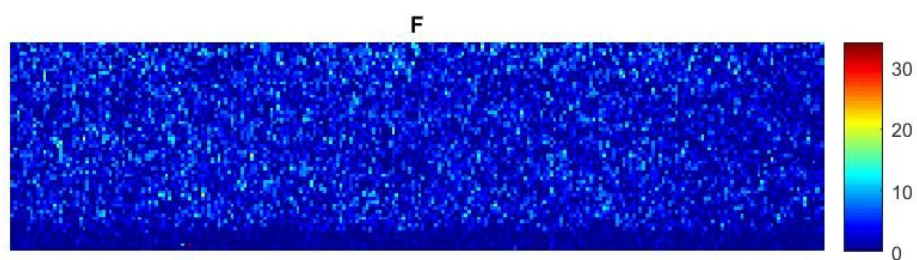
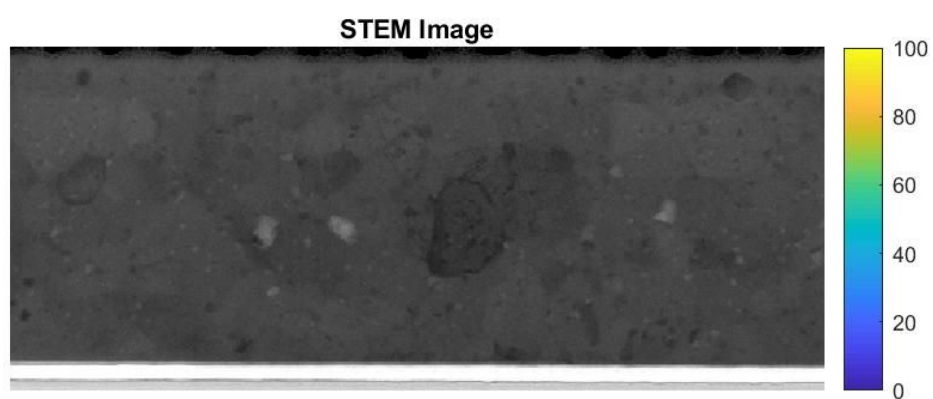
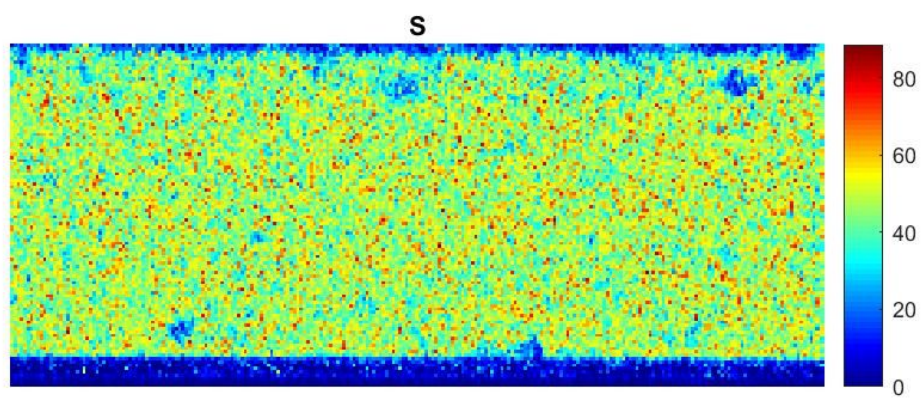
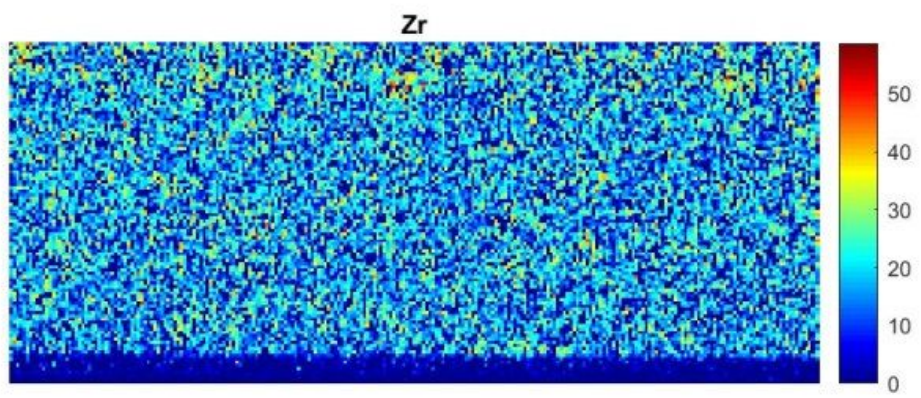
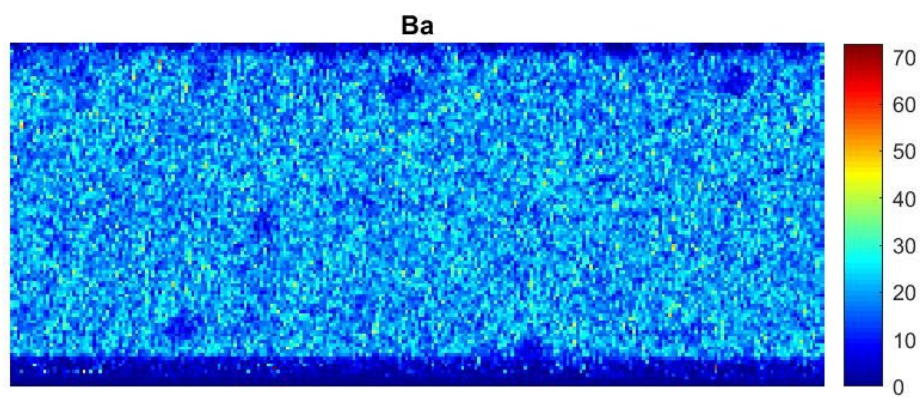
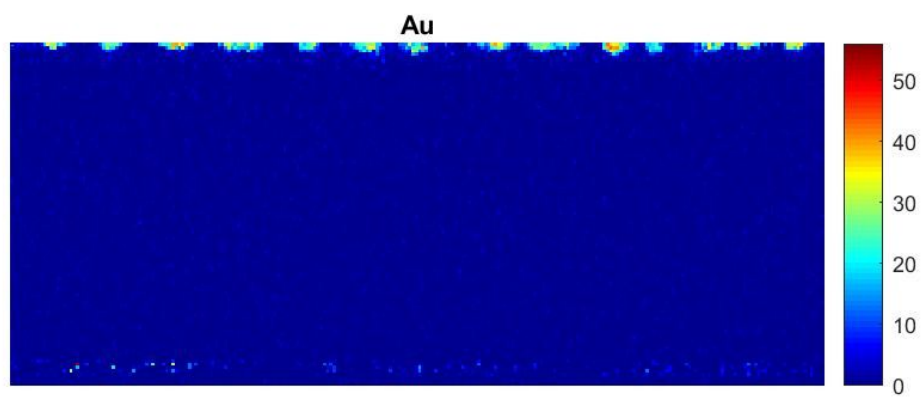
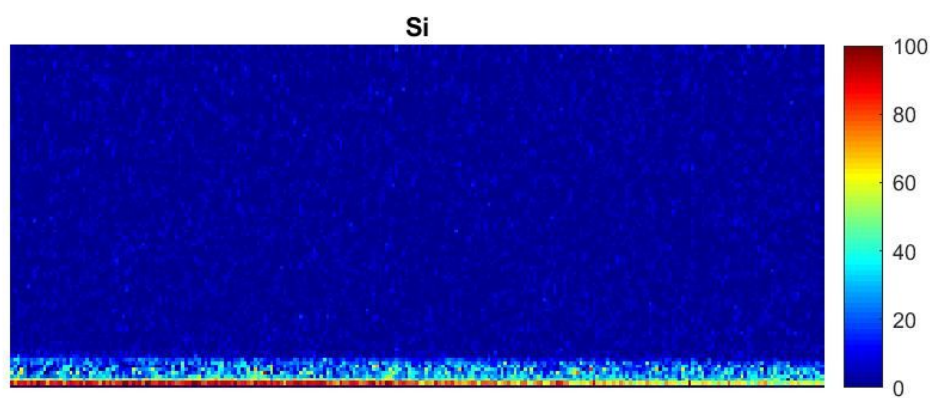
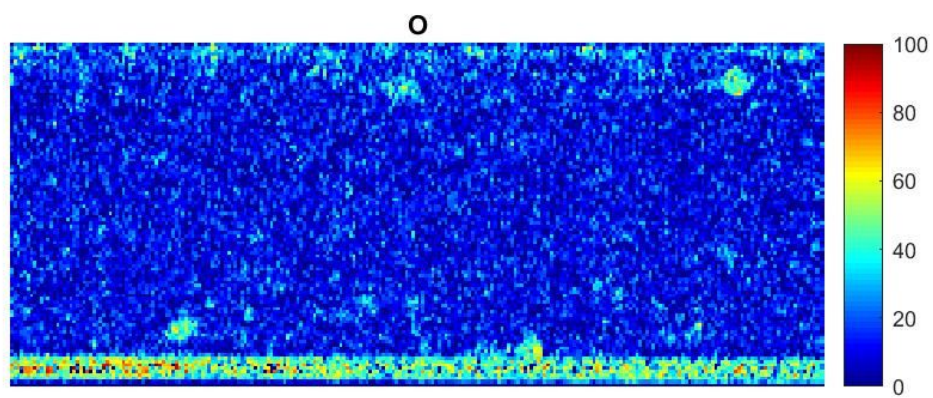


Figure S2. STEM bright field image measured at 120° on a compositionally graded sample annealed at 900°C ; EDS maps of different elements recorded on the same area where STEM was performed.







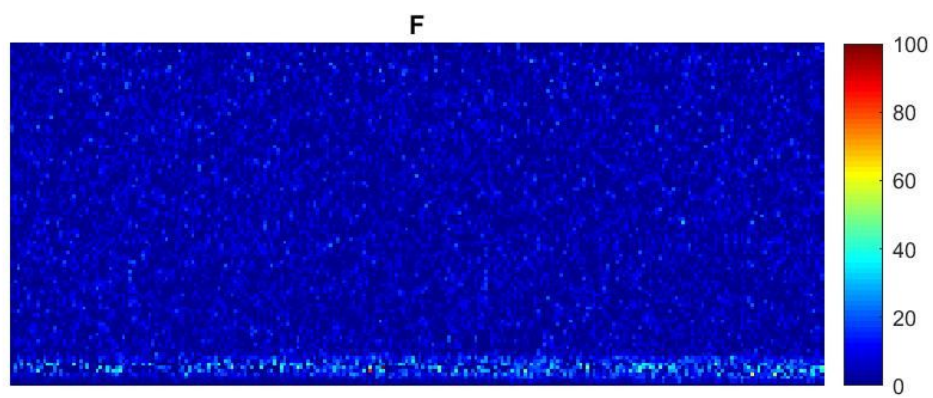
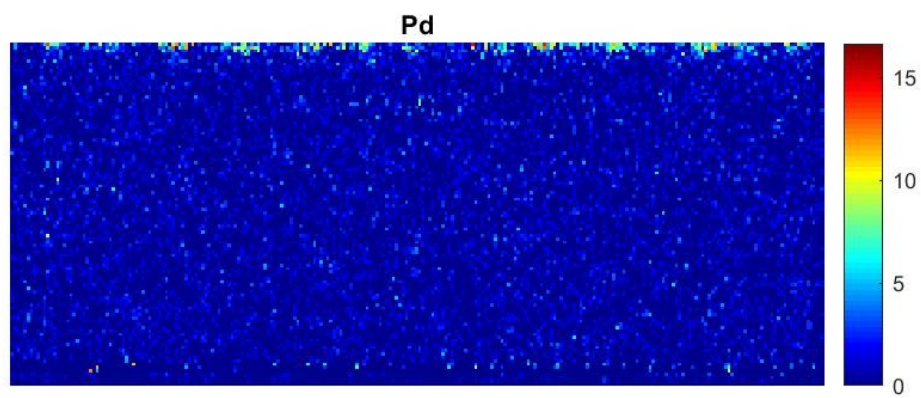
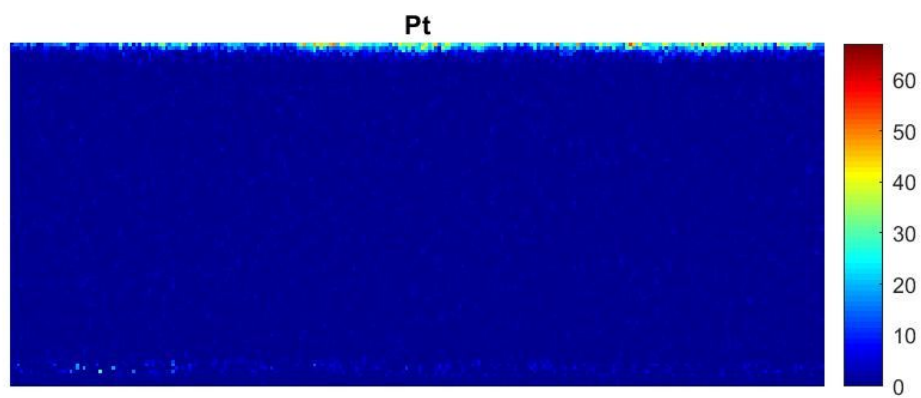


Figure S3. STEM bright field image measured at 180° on a compositionally graded sample annealed at 900°C ; EDS maps of different elements recorded on the same where STEM was performed.